

# Ikuo Suemune

## List of Publications by Citations

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#	Paper	IF	Citations
313	Reexamination of N composition dependence of coherently grown GaNAs band gap energy with high-resolution x-ray diffraction mapping measurements. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1254-1256	3.4	221
312	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 1378-1380	3.4	185
311	Comment on Polarization Dependent Momentum Matrix Elements in Quantum Well Lasers. <i>Japanese Journal of Applied Physics</i> , <b>1984</b> , 23, L35-L36	1.4	176
310	Growth and characterization of hypothetical zinc-blende ZnO films on GaAs(001) substrates with ZnS buffer layers. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 550-552	3.4	175
309	. <i>IEEE Journal of Quantum Electronics</i> , <b>1988</b> , 24, 1778-1790	2	116
308	Nitrogen-Doped p-Type ZnO Layers Prepared with H <sub>2</sub> O Vapor-Assisted Metalorganic Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, L1281-L1284	1.4	115
307	Luminescent porous silicon synthesized by visible light irradiation. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1429-1431	3.4	114
306	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 3021-3023	3.4	105
305	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	104
304	Temperature dependence of band gap energies of GaAsN alloys. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1285-1287	3.4	96
303	. <i>IEEE Journal of Quantum Electronics</i> , <b>1990</b> , 26, 213-216	2	91
302	Self-ordering of nanofacets on vicinal SiC surfaces. <i>Physical Review Letters</i> , <b>2003</b> , 91, 226107	7.4	81
301	. <i>IEEE Journal of Quantum Electronics</i> , <b>1991</b> , 27, 1149-1159	2	66
300	Quantum Mechanical Size Effect Modulation Light Sources -- A New Field Effect Semiconductor Laser or Light Emitting Device. <i>Japanese Journal of Applied Physics</i> , <b>1983</b> , 22, L22-L24	1.4	66
299	Controllable enhancement of excitonic spontaneous emission by quantum confined Stark effect in GaAs quantum wells embedded in quantum microcavities. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 2735-2737	3.4	53
298	Study of Luminescent Region in Anodized Porous Silicons by Photoluminescence Imaging and Their Microstructures. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L490-L493	1.4	52
297	Bandgap Energy of GaNAs Alloys Grown on (001) GaAs by Metalorganic Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, L1572-L1575	1.4	49

296	Position controlled nanowires for infrared single photon emission. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 1711-1713	3.6	47
295	Analysis of temperature dependent optical gain of strained quantum well taking account of carriers in the SCH layer. <i>IEEE Photonics Technology Letters</i> , <b>1994</b> , 6, 344-347	2.2	47
294	Extremely-low-threshold and high-temperature operation in a photopumped ZnSe/ZnSSe blue laser. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 1401-1403	3.4	46
293	Incidence angle effect of a hydrogen plasma beam for the cleaning of semiconductor surfaces. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 760-762	3.4	45
292	Field effects on the refractive index and absorption coefficient in AlGaAs quantum well structures and their feasibility for electrooptic device applications. <i>IEEE Journal of Quantum Electronics</i> , <b>1987</b> , 23, 2167-2180	2	45
291	Photoirradiation Effect on Photoluminescence from Anodized Porous Silicons and Luminescence Mechanism. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L494-L497	1.4	43
290	Blue-light stimulated emission from a localized state formed by well-barrier fluctuation in a II-VI semiconductor superlattice. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 1182-1184	3.4	43
289	Luminescence properties of ZnO films grown on GaAs substrates by molecular-beam epitaxy excited by electron-cyclotron resonance oxygen plasma. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 280-283	1.6	42
288	Growth and luminescence properties of self-organized ZnSe quantum dots. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 235-237	3.4	42
287	Epitaxial growth of zinc-blende ZnSe/MgS superlattices on (001) GaAs. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 844-846	3.4	41
286	Role of ZnS buffer layers in growth of zincblende ZnO on GaAs substrates by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 435-439	1.6	38
285	Nucleation and growth kinetics of AlN films on atomically smooth 6H-SiC (0001) surfaces. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3612-3614	3.4	38
284	Lasing in a ZnS <sub>0.12</sub> Se <sub>0.88</sub> /ZnSe multilayer structure with photopumping. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 981-983	3.4	38
283	Effect of indium doping on the transient optical properties of GaN films. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 2879-2881	3.4	35
282	Mass Spectrometric Study and Modeling of Decomposition Process of Tris-Dimethylamino-Arsenic on (001) GaAs Surface. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, L1579-L1582	1.4	35
281	Characterization of Nitrogen-Doped ZnSe and ZnS <sub>0.06</sub> Se <sub>0.94</sub> Films Grown by Metal-Organic Vapor-Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, L2195-L2198	1.4	35
280	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	34
279	Deterministic Single-Photon and Polarization-Correlated Photon Pair Generations From a Single InAlAs Quantum Dot. <i>Journal of Nanoelectronics and Optoelectronics</i> , <b>2006</b> , 1, 39-51	1.3	34

278	Growth and structural characterization of III $\bar{N}$ IV semiconductor alloys. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 755-761	1.8	33
277	Luminescence of a cooper pair. <i>Physical Review Letters</i> , <b>2009</b> , 103, 187001	7.4	31
276	Stability of CdSe and ZnSe dots self-organized on semiconductor surfaces. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 3886-3888	3.4	31
275	Metalorganic molecular beam epitaxy of GaNAs alloys on (0 0 1)GaAs. <i>Journal of Crystal Growth</i> , <b>1998</b> , 189-190, 490-495	1.6	31
274	Superconductor-Based Quantum-Dot Light-Emitting Diodes: Role of Cooper Pairs in Generating Entangled Photon Pairs. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 9264-9271	1.4	31
273	Low-temperature GaAs epitaxial growth using electron-cyclotron resonance/metalorganic-molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>1988</b> , 64, 2778-2780	2.5	31
272	Surface-emitting stimulated emission in high-quality ZnO thin films. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 3733-3736	2.5	30
271	High Output Power (>20 W) and High Quantum Efficiency in a Photopumped ZnSe/ZnS $\bar{S}$ e Blue Laser Operating at Room Temperature. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, L1399-L1401	1.4	30
270	In-SituRHEED Monitoring of Hydrogen Plasma Cleaning on Semiconductor Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, 2273-2276	1.4	30
269	Field-induced modulations of refractive index and absorption coefficient in a GaAs/AlGaAs quantum well structure. <i>Electronics Letters</i> , <b>1986</b> , 22, 888	1.1	30
268	New low-temperature process for growth of GaAs on Si with metalorganic molecular beam epitaxy assisted by a hydrogen plasma. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 2173-2175	3.4	29
267	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 033506	2.5	28
266	Photoluminescence study of InAs quantum dots embedded in GaNAs strain compensating layer grown by metalorganic-molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 6813-6818	2.5	28
265	Enhanced photon generation in a Nb/n-InGaAs/p-InP superconductor/semiconductor-diode light emitting device. <i>Physical Review Letters</i> , <b>2011</b> , 107, 157403	7.4	26
264	Single-crystalline rocksalt CdO layers grown on GaAs (001) substrates by metalorganic molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 470-472	3.4	26
263	Improvement of InAs quantum-dot optical properties by strain compensation with GaNAs capping layers. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4524-4526	3.4	25
262	Noncontact photoacoustic measurements of semiconductors with Michelson interferometry. <i>Journal of Applied Physics</i> , <b>1985</b> , 58, 615-617	2.5	25
261	Microcavities with distributed Bragg reflectors based on ZnSe/MgS superlattice grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 699-703	1.6	24

260	Atomic layer epitaxy of GaAs and role of As-source materials on self-limiting mechanism. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 1498-1500	3-4	24
259	Single-photon emission in telecommunication band from an InAs quantum dot grown on InP with molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 061114	3-4	23
258	Epitaxial ZnO growth and p-type doping with MOMBE. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 640-647	1-3	23
257	Photon-spin qubit-conversion based on Overhauser shift of Zeeman energies in quantum dots. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 112506	3-4	23
256	Electroreflectance Spectra and Field-Induced Variation in Refractive Index of a GaAs/AlAs Quantum Well Structure at Room Temperature. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L640-L642	1-4	23
255	Self-Organized CdSe Quantum Dots on (100)ZnSe/GaAs Surfaces Grown by Metalorganic Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4097-4101	1-4	22
254	Near-Room-Temperature Photopumped Blue Lasers in ZnS <sub>x</sub> Se <sub>1-x</sub> /ZnSe Multilayer Structures. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L2420-L2422	1-4	22
253	Photon Antibunching Observed from an InAlAs Single Quantum Dot. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L793-L796	1-4	21
252	Semiconductor photonic dots: Visible wavelength-sized optical resonators. <i>Applied Physics Letters</i> , <b>1999</b> , 74, 1963-1965	3-4	21
251	X-ray photoelectron spectroscopy and atomic force microscopy surface study of GaAs(100) cleaning procedures. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1995</b> , 13, 77		21
250	Transient Response of Photoluminescence for Electric Field in a GaAs/Al <sub>0.7</sub> Ga <sub>0.3</sub> As Single Quantum Well: Evidence for Field-Induced Increase in Carrier Life Time. <i>Japanese Journal of Applied Physics</i> , <b>1985</b> , 24, L586-L588	1-4	21
249	Gain-switching characteristics and fast transient response of three-terminal size-effect modulation laser. <i>IEEE Journal of Quantum Electronics</i> , <b>1986</b> , 22, 1900-1908	2	21
248	Strain effect on the N composition dependence of GaNAs bandgap energy grown on (0 0 1) GaAs by metalorganic molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 355-358	1-6	20
247	Superconductor-based Light Emitting Diode: Demonstration of Role of Cooper Pairs in Radiative Recombination Processes. <i>Applied Physics Express</i> , <b>2008</b> , 1, 011701	2-4	19
246	Theory of strain states in InAs quantum dots and dependence on their capping layers. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 063502	2-5	19
245	Highly conductive GaAsNSe alloys grown on GaAs and their nonalloyed ohmic properties. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3284-3286	3-4	19
244	H <sub>2</sub> O-Vapor-Activated ZnO Growth on a-Face Sapphire Substrates by Metalorganic Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 2851-2854	1-4	19
243	Optical and structural characterizations of ZnSe/ZnS <sub>2</sub> superlattices grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 3029-3033	2-5	19

242	Bright single-photon source based on an InAs quantum dot in a silver-embedded nanocone structure. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 131114	3.4	18
241	A Cooper-Pair Light-Emitting Diode: Temperature Dependence of Both Quantum Efficiency and Radiative Recombination Lifetime. <i>Applied Physics Express</i> , <b>2010</b> , 3, 054001	2.4	18
240	GaNAs as Strain Compensating Layer for 1.55 $\mu\text{m}$ Light Emission from InAs Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, 5598-5601	1.4	18
239	Selective Formation of luminescent porous silicon by photosynthesis. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 4765-4767	2.5	18
238	Optical properties of highly excited ZnSe/ZnS <sub>x</sub> Se <sub>1-x</sub> multiple-quantum-well structures. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 681-685	1.8	18
237	Lattice-Mismatch Enhanced Diffusion at a ZnSe/GaAs Interface - Increase of Thermal Stability in a Lattice-Matching System. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L2072-L2075	1.4	18
236	Excitonic properties of zinc-blende ZnSe/MgS superlattices studied by reflection spectroscopy. <i>Physical Review B</i> , <b>1997</b> , 55, 4449-4455	3.3	17
235	Control of ZnSe Film Stoichiometry at ZnSe/GaAs Interface Grown by MOCVD. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L827-L829	1.4	17
234	Anomalous dip observed in intensity autocorrelation function as an inherent nature of single-photon emitters. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 161107	3.4	16
233	Excitonic luminescence up to room temperature in a ZnSe/MgS superlattice. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 2350-2352	3.4	16
232	GaN Quantum Structures with Fractional Dimension [From Quantum Well to Quantum Dot]. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 216, 431-434	1.3	15
231	Atomic layer epitaxy of AlAs using trimethylamine-alane and amino-As. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1420-1422	3.4	15
230	Excitonic properties of ZnSe/ZnSeS superlattices. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 2439-2441	3.4	15
229	Switching of photoluminescence by pulsed electric field in GaAs/Al <sub>0.7</sub> Ga <sub>0.3</sub> As single quantum well structure. <i>IEEE Journal of Quantum Electronics</i> , <b>1986</b> , 22, 1837-1844	2	15
228	Enhanced Photon Extraction from a Quantum Dot Induced by a Silver Microcolumnar Photon Reflector. <i>Applied Physics Express</i> , <b>2013</b> , 6, 062801	2.4	14
227	Low-Dimensional III-V Semiconductor Structures: ZnSe/MgS Superlattices and CdSe Self-Organized Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>1997</b> , 202, 845-856	1.3	14
226	Atomic force microscope lithography on carbonaceous films deposited by electron-beam irradiation. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 716-718	3.4	14
225	Electron effective mass and mobility in heavily doped n-GaN probed by Raman scattering. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 103528	2.5	14

224	CdO epitaxial layers grown on (0 0 1) GaAs surfaces by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 518-522	1.6	14
223	Study of current-voltage characteristic in a ZnSe-based II-VI laser diode. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 2612-2614	3.4	14
222	Catalytic Precracking of Amino-As in Metalorganic Molecular-Beam Epitaxy of GaAs. <i>Japanese Journal of Applied Physics</i> , <b>1992</b> , 31, L1272-L1275	1.4	14
221	Quantum-confined field-effect light emitters with high-speed switching capability. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1149-1151	3.4	14
220	Band-edge hole mass in strained-quantum-well structures. <i>Physical Review B</i> , <b>1991</b> , 43, 14099-14106	3.3	14
219	Metal-coated semiconductor nanostructures and simulation of photon extraction and coupling to optical fibers for a solid-state single-photon source. <i>Nanotechnology</i> , <b>2013</b> , 24, 455205	3.4	13
218	Room temperature ultraviolet lasing action in high-quality ZnO thin films. <i>Journal of Luminescence</i> , <b>2007</b> , 122-123, 828-830	3.8	13
217	Continuous-Wave Operation of a Lateral Current Injection Ridge Waveguide AlGaAs/GaAs Laser with a Selectively-Doped Heterostructure. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 990-991	1.4	13
216	Observation of optical bistability by charge-induced self-feedback in biased AlGaAs multiple quantum well structures. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 419-421	3.4	13
215	Thermal stability of nearly lattice-matched ZnSse/GaAs interface grown by MOVPE. <i>Journal of Crystal Growth</i> , <b>1988</b> , 93, 662-666	1.6	13
214	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. <i>Applied Physics Express</i> , <b>2016</b> , 9, 032801	2.4	13
213	Atomic Force Microscope Nanolithography on SiO <sub>2</sub> /Semiconductor Surfaces. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4057-4060	1.4	12
212	Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 277-280	1.6	12
211	Nucleation Stages of Carbon Nanotubes on SiC(0001) by Surface Decomposition. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L803-L805	1.4	12
210	Formation of wire-like surfaces and lateral composition modulation in GaAsN grown by metalorganic molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 546-550	1.6	12
209	Atomic force microscope based patterning of carbonaceous masks for selective area growth on semiconductor surfaces. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 3158-3165	2.5	12
208	Desorption properties of amine species during atomic layer epitaxy of GaAs using amino-As. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 2577-2579	3.4	12
207	Auger effects in acceptor-doped long-wavelength strained quantum well lasers. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 2579-2581	3.4	12

206	Photopumped lasing in ZnS <sub>Se</sub> /ZnSe multilayer structures up to 210 K. <i>Journal of Crystal Growth</i> , <b>1990</b> , 101, 754-757	1.6	12
205	Photoacoustic study of surface and bulk nonradiative recombinations in GaAs with two-wavelength excitations. <i>Journal of Applied Physics</i> , <b>1986</b> , 60, 2621-2623	2.5	12
204	Size effect modulation light sources [Possibility of LED mode operation at room temperature. <i>Superlattices and Microstructures</i> , <b>1985</b> , 1, 335-337	2.8	12
203	Quenching of photoluminescence from GaAs/AlGaAs single quantum well by an electric field at high temperature. <i>Superlattices and Microstructures</i> , <b>1985</b> , 1, 111-113	2.8	12
202	Electric Field Effect on Subband State Transitions Peaks in the Photoluminescence from a GaAlAs Quantum Well Structure. <i>Japanese Journal of Applied Physics</i> , <b>1985</b> , 24, L589-L592	1.4	12
201	1.55 $\mu$ m emission from GaInNAs with indium-induced increase of N concentration. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1992-1994	3.4	11
200	Structural anisotropy in GaN films grown on vicinal 4H-SiC surfaces by metallorganic molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1569-1571	3.4	11
199	Low-Temperature Selective Growth of ZnSe and ZnS on (001) GaAs Patterned with Carbonaceous Mask by Metalorganic Molecular-Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, L272-L274 <sup>1.4</sup>	1.4	11
198	X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution. <i>Applied Surface Science</i> , <b>1994</b> , 82-83, 250-256	6.7	11
197	Room-temperature stimulated emission in optically pumped narrow ZnSe/ZnS <sub>x</sub> Se <sub>1-x</sub> multiple-quantum-well structures. <i>Journal of Applied Physics</i> , <b>1992</b> , 72, 4969-4971	2.5	11
196	Photopumped ZnSe/ZnS <sub>Se</sub> blue semiconductor lasers and a theoretical calculation of the optical gain. <i>Journal of Crystal Growth</i> , <b>1992</b> , 117, 1068-1072	1.6	11
195	Room-temperature operation of three-terminal quantum-confined field-effect light emitters. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 2059-2061	3.4	11
194	Two-Dimensionally Collimated Output Beam from GaAlAs Diode Lasers with Two-Dimensional Distributed Bragg Reflectors. <i>Japanese Journal of Applied Physics</i> , <b>1983</b> , 22, L267-L269	1.4	11
193	Analysis of Intrinsic Saturable Absorption in InGaAs/InP Diode Lasers. <i>Japanese Journal of Applied Physics</i> , <b>1981</b> , 20, L635-L638	1.4	11
192	Strongly suppressed multi-photon generation from a single quantum dot in a metal-embedded structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 337-339		10
191	Formation of ohmic contacts to p-type ZnO. <i>Physica Status Solidi (B): Basic Research</i> , <b>2004</b> , 241, 635-639	1.3	10
190	Excitonic properties in ZnSe/ZnS <sub>x</sub> Se <sub>1-x</sub> strained-layer superlattices by one- and two-photon spectroscopy. <i>Physical Review B</i> , <b>1994</b> , 49, 14367-14371	3.3	10
189	Large estimated frequency response increase from deep potential well strained quantum well lasers. <i>IEEE Photonics Technology Letters</i> , <b>1994</b> , 6, 1315-1317	2.2	10



188	Doping in a superlattice structure: Improved hole activation in wide-gap II-VI materials. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 2364-2369	2.5	10
187	Selectively doped double-heterojunction lateral current injection ridge waveguide AlGaAs/GaAs laser. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1391-1393	3.4	10
186	. <i>IEEE Photonics Technology Letters</i> , <b>1990</b> , 2, 881-883	2.2	10
185	A 140 ps Optical Pulse Generation by Field-Induced Gain Switching in a Photo-Excited Quantum Well Laser. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L117-L119	1.4	10
184	Stability and interdiffusion at MOCVD grown ZnSe/GaAs interfaces. <i>Journal of Crystal Growth</i> , <b>1988</b> , 86, 467-470	1.6	10
183	Polarization dependent absorption spectra in quantum wire structures. <i>Superlattices and Microstructures</i> , <b>1988</b> , 4, 19-22	2.8	10
182	Spectral hole burnings at high energy tails in spontaneous emission and hot carrier relaxation in InGaAsP lasers. <i>IEEE Journal of Quantum Electronics</i> , <b>1983</b> , 19, 924-929	2	10
181	Observation of Acoustic Signals from Semiconductor Lasers. <i>Japanese Journal of Applied Physics</i> , <b>1981</b> , 20, L9-L12	1.4	10
180	Fiber-Based Bidirectional Solid-State Single-Photon Emitter Based on Semiconductor Quantum Dot. <i>Applied Physics Express</i> , <b>2013</b> , 6, 065203	2.4	9
179	Transport characteristics of a superconductor-based LED. <i>Superconductor Science and Technology</i> , <b>2010</b> , 23, 034025	3.1	9
178	Exciton coherence in clean single InP/InAsP/InP nanowire quantum dots emitting in infra-red measured by Fourier spectroscopy. <i>Journal of Physics: Conference Series</i> , <b>2009</b> , 193, 012132	0.3	9
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42	Single photon emission with high degree of circular polarization from a single quantum dot under zero magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1824-1827	3	1
41	SiC Surface Nanostructures Induced by Self-Ordering of Nano-Facets. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 407-410	0.4	1
40	Observation of reflection high-energy electron diffraction oscillation during MOMBE growth of AlAs and related modulated semiconductor structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 756-760	3	1
39			1
38	New type of ZnCdS/ZnMgCdS heterostructures lattice-matched to GaAs for selective-area growth. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 125-129	1.6	1
37	Enhancement of spontaneous emission by ZnS-based II-VI semiconductor photonic dots. <i>Journal of Crystal Growth</i> , <b>2000</b> , 214-215, 1024-1028	1.6	1
36	Three-photon absorption coefficients in ZnSe/ZnS <sub>0.18</sub> Se <sub>0.82</sub> strained-layer superlattices. <i>Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics</i> , <b>1996</b> , 18, 465-469		1
35	One- and two-phonon scattering processes in ZnSe/ZnS <sub>x</sub> Se <sub>1-x</sub> superlattices studied by micro-Raman spectroscopy. <i>Physical Review B</i> , <b>1994</b> , 50, 4988-4991	3.3	1
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33	Comparison of triethylgallium and its amine-adduct on gas-phase reaction with trimethylamine-alane. <i>Journal of Crystal Growth</i> , <b>1994</b> , 136, 152-156	1.6	1
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